

ABSTRACT**AZEOTROPIC MIXTURE OF FLUOROMETHANE AND HYDROGEN
CHLORIDE AND PROCESS FOR PURIFYING FLUOROMETHANE**

It is an object of the present invention to provide a method capable of efficiently producing high-purity HFC-41 which can be used as an etching gas for semiconductors. The process for purifying fluoromethane of the present invention comprises distilling a mixture containing fluoromethane and hydrogen chloride to distill out fluoromethane from the top of distillation column and obtain an azeotropic mixture of fluoromethane and hydrogen chloride from the bottom of the distillation column.

(FIG. 1)